

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

| | |
|-------------|----------|
| $I_{F(AV)}$ | 2 x 20 A |
| V_{RRM} | 40 V |
| $T_j (max)$ | 150 °C |
| $V_F (max)$ | 0.49 V |

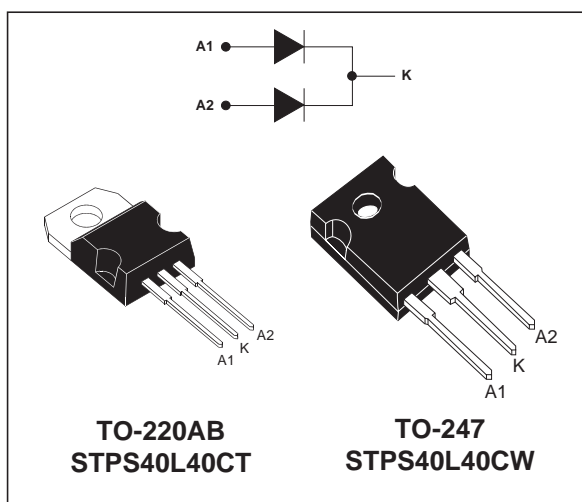
FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and DC to DC converters.

Packaged in TO-220AB and TO-247 this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

| Symbol | Parameter | | | Value | Unit |
|---------------------|--|--|-------------------------|---------------|------|
| V _{RRM} | Repetitive peak reverse voltage | | | 40 | V |
| I _{F(RMS)} | RMS forward current | | | 30 | A |
| I _{F(AV)} | Average forward current | T _c = 130°C δ = 0.5 | Per diode Per device | 20 40 | A |
| I _{FSM} | Surge non repetitive forward current | t _p = 10 ms Sinusoidal | | 230 | A |
| I _{RRM} | Repetitive peak reverse current | t _p = 2 μs square F = 1kHz | | 2 | A |
| I _{RSM} | Non repetitive peak reverse current | t _p = 100 μs square | | 3 | A |
| P _{ARM} | Repetitive peak avalanche power | t _p = 1μs T _j = 25°C | | 8100 | W |
| T _{stg} | Storage temperature range | | | - 65 to + 150 | °C |
| T _j | Maximum operating junction temperature * | | | 150 | °C |
| dV/dt | Critical rate of rise of reverse voltage | | | 10000 | V/μs |

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS40L40CT/CW

THERMAL RESISTANCES

| Symbol | Parameter | | Value | Unit |
|---------------|------------------|-----------|-------|------|
| $R_{th(j-c)}$ | Junction to case | Per diode | 1.5 | °C/W |
| | | Total | 0.8 | |
| $R_{th(c)}$ | | Coupling | 0.1 | °C/W |

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

| Symbol | Parameter | Tests Conditions | | Min. | Typ. | Max. | Unit |
|---------|-------------------------|---------------------------|---------------------|------|------|------|------|
| I_R^* | Reverse leakage current | $T_j = 25^\circ\text{C}$ | $V_R = V_{RRM}$ | | | 0.8 | mA |
| | | $T_j = 100^\circ\text{C}$ | | | 30 | 70 | mA |
| V_F^* | Forward voltage drop | $T_j = 25^\circ\text{C}$ | $I_F = 20\text{ A}$ | | | 0.53 | V |
| | | $T_j = 125^\circ\text{C}$ | $I_F = 20\text{ A}$ | | 0.42 | 0.49 | |
| | | $T_j = 25^\circ\text{C}$ | $I_F = 40\text{ A}$ | | | 0.69 | |
| | | $T_j = 125^\circ\text{C}$ | $I_F = 40\text{ A}$ | | 0.6 | 0.7 | |

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.28 \times I_{F(AV)} + 0.0105 I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

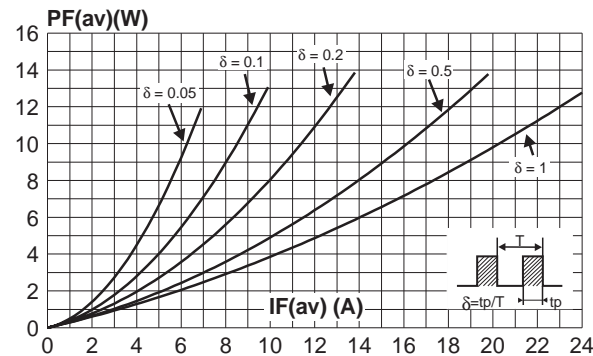


Fig. 3: Normalized avalanche power derating versus pulse duration.

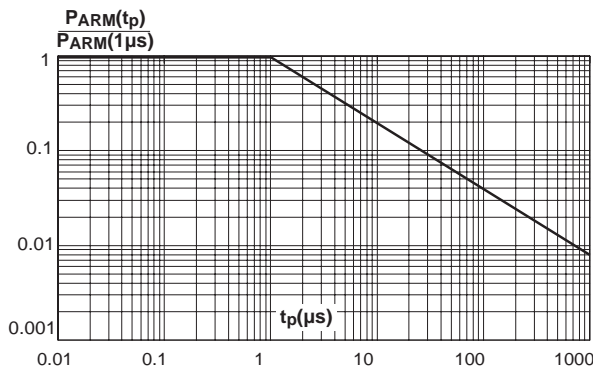


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$, per diode).

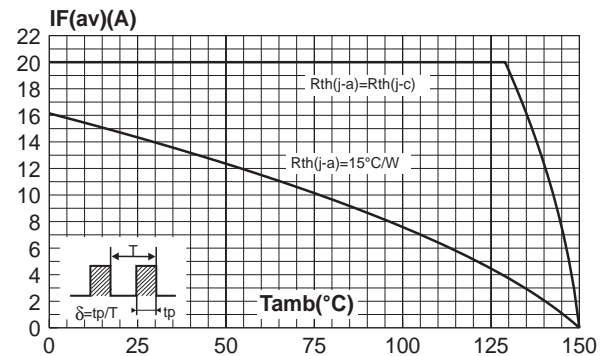


Fig. 4: Normalized avalanche power derating versus junction temperature.

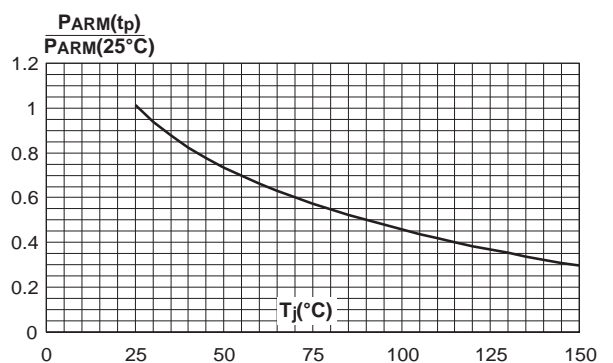


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

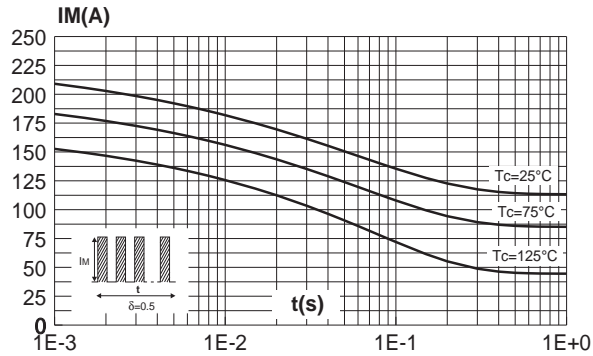


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

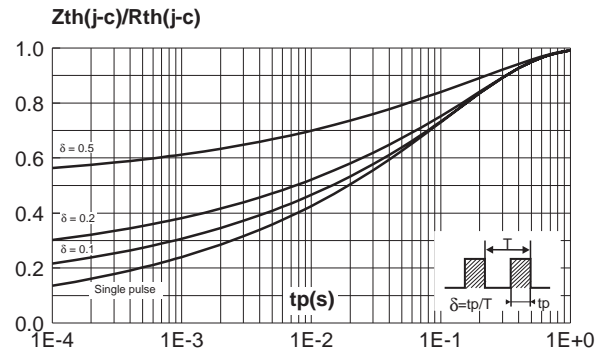


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

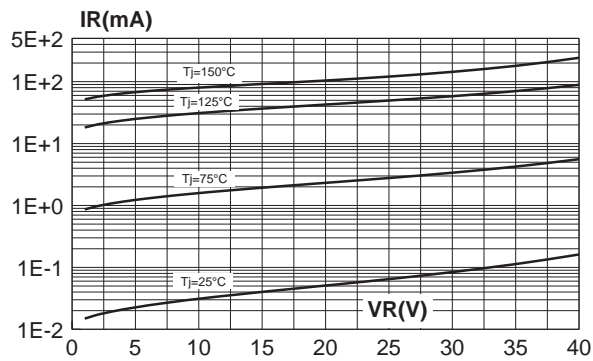


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

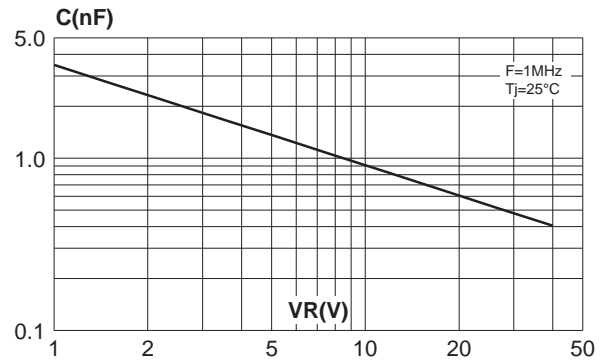
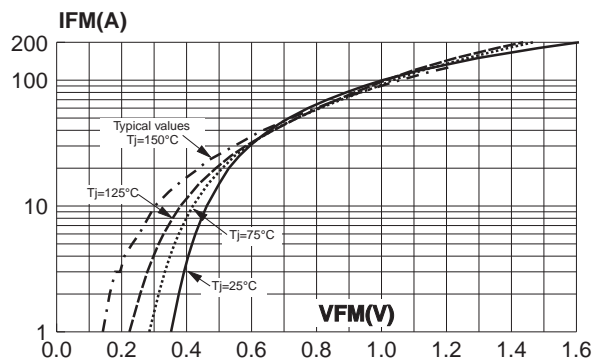
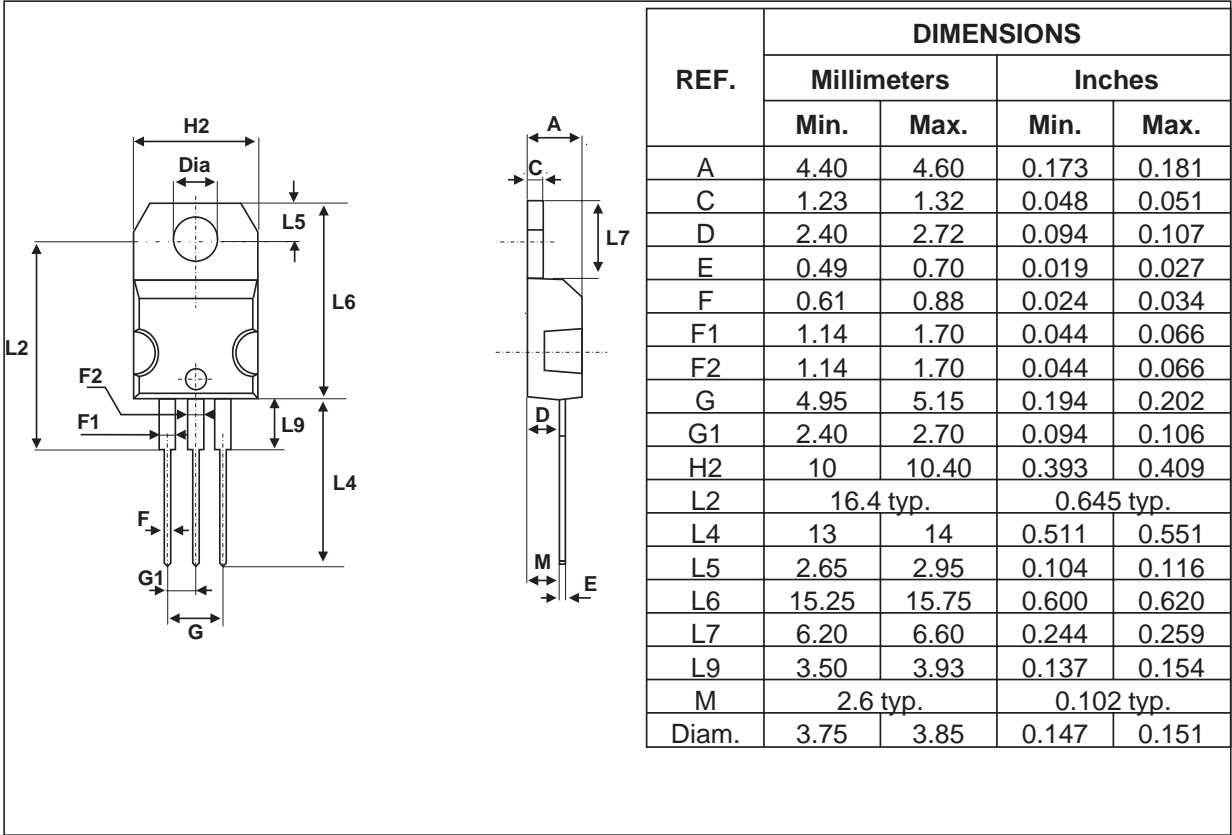


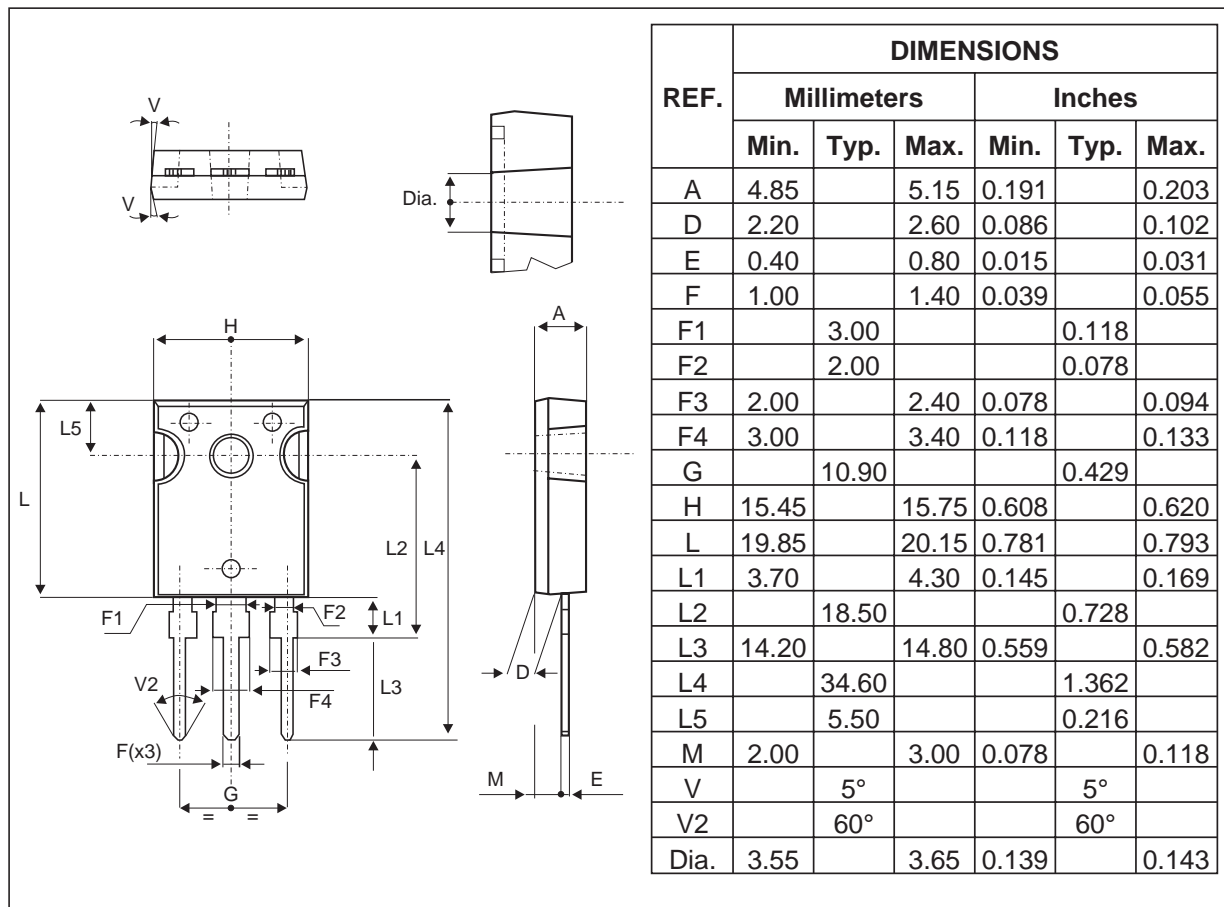
Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).



PACKAGE MECHANICAL DATA
TO-220AB



- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.55M.N
- MAXIMUM TORQUE VALUE : 0.70 M.N

PACKAGE MECHANICAL DATA
TO-247


- COOLING METHOD : C
- RECOMMENDED TORQUE VALUE : 0.8M.N
- MAXIMUM TORQUE VALUE : 1.0M.N

| Ordering type | Marking | Package | Weight | Base qty | Delivery mode |
|---------------|-------------|----------|--------|----------|---------------|
| STPS40L40CT | STPS40L40CT | TO-220AB | 2g | 50 | Tube |
| STPS40L40CW | STPS40L40CW | TO-247 | 4.4g | 30 | Tube |

- EPOXY MEETS UL94,V0

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